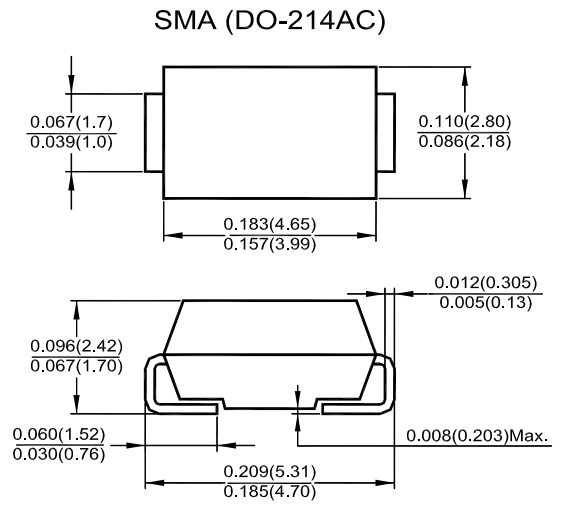


RB161L-40

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE FOR HIGH FREQUENCY RECTIFICATION AND SWITCHING POWER SUPPLY

Features

- Compact power mold type
- Ultra low V_F
- $V_{RM} = 40$ V guaranteed



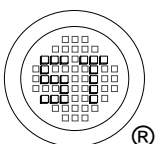
Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, resistive or inductive load, For capacitive load, derate by 20%

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Blocking Voltage	V_R	20	V
Mean Rectifying Current ¹⁾	I_O	1	A
Peak Forward Surge Current	I_{FSM}	70	A
Maximum Forward Voltage at $I_F = 1$ A	V_F	0.4	V
Maximum Reverse Current at $V_R = 20$ V	I_R	1	mA
Operating Junction Temperature Range	T_J	125	°C
Storage Temperature Range	T_S	- 40 to + 125	°C

¹⁾ When mounting on PCB



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 14/04/2008

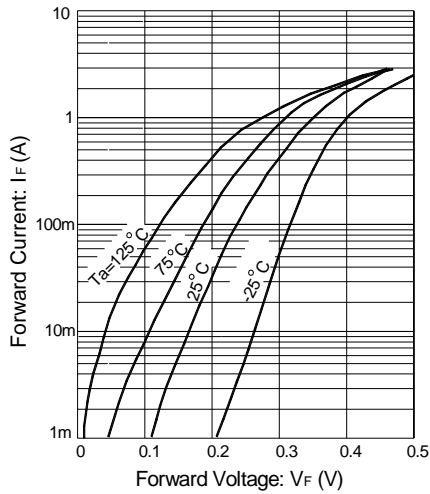


Fig. 1 Forward Characteristics

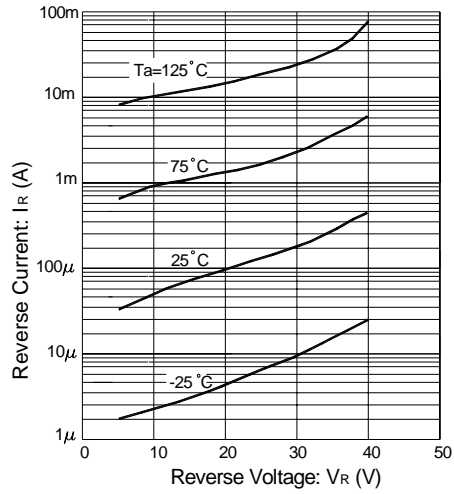


Fig. 2 Reverse Characteristics

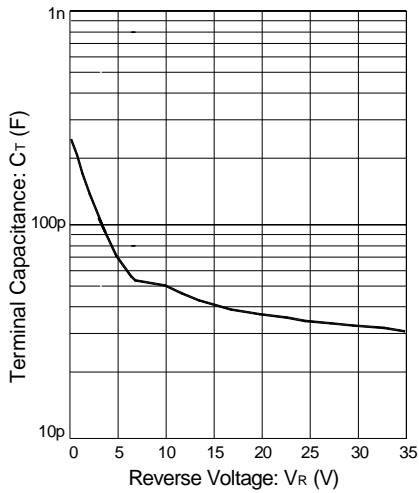
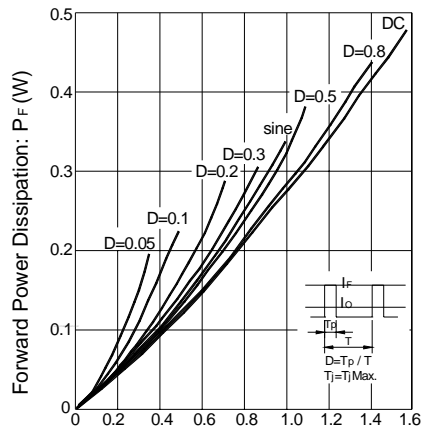


Fig. 3 Capacitance Between Terminals Characteristics



Average Rectified Forward Current: I_o

Fig. 4 Forward Power Dissipation Characteristics

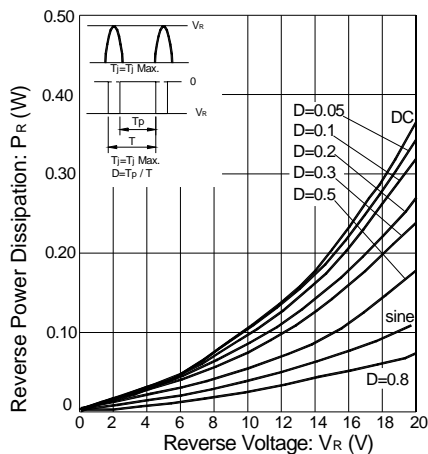


Fig. 5 Reverse Power Dissipation Characteristics

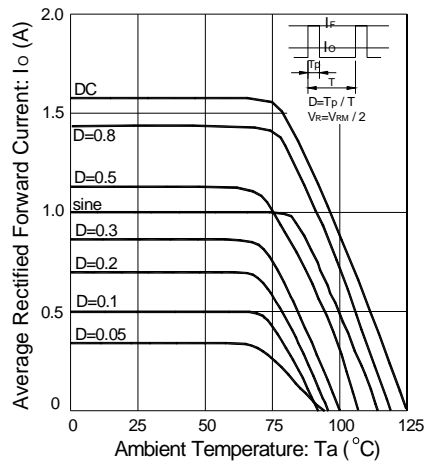
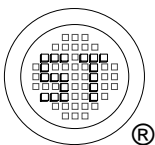


Fig. 6 Derating Curve (When Mounting On Glass Epoxy PCBs)



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098